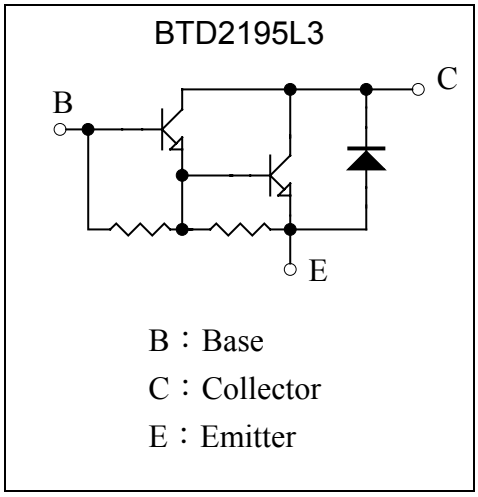
NPN Epitaxial Planar Transistor

BTD2195L3

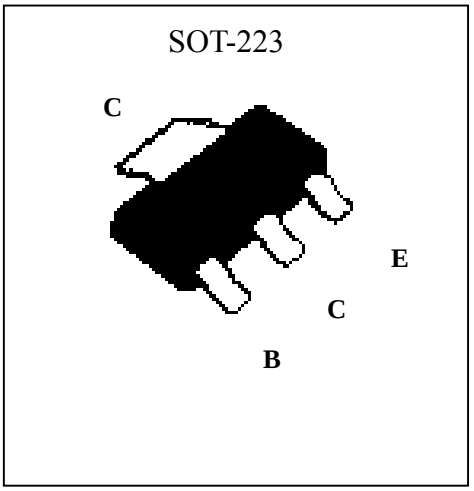
Description

The BTD2195L3 is a NPN Darlington transistor, designed for use in general purpose amplifier and low speed switching application. Pb-free package process is adopted.

Equivalent Circuit



Outline



Ordering Information

Device	Package	Shipping
BTD2195L3-0-T3-X	SOT-223 (Pb-free lead plating package)	2500 pcs / tape & reel

Environment friendly grade : S for RoHS compliant products, G for RoHS compliant and green compound products

Packing spec, T3 : 2500 pcs / tape & reel, 13” reel

Product rank, zero for no rank products

Product name

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V_{CBO}	130	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current (DC)	I_C	4	A
Collector Current (Pulse)	I_{CP}	6 (Note)	A
Power Dissipation @ T_C=25℃	Pd	5	W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	25	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

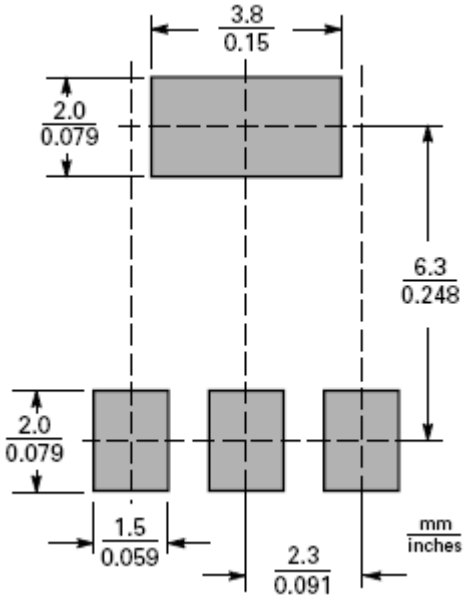
Note : Single Pulse Pw≦350μs, Duty≦2%.

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CEO}	120	-	-	V	I_C=1mA, I_B=0
BV_{CBO}	140	-	-	V	I_C=100μA, I_E=0
I_{CBO}	-	-	100	μA	V_{CB}=100V, I_E=0
I_{CEO}	-	-	100	μA	V_{CE}=100V, I_E=0
I_{EBO}	-	-	2	mA	V_{EB}=5V, I_C=0
*$V_{CE(sat)}$	-	-	2.5	V	I_C=2A, I_B=2mA
*$V_{BE(on)}$			2.3	V	V_{CE}=4V, I_C=2A
*$h_{FE}1$	1000	-	-	-	V_{CE}=4V, I_C=1A
*$h_{FE}2$	500	-	-	-	V_{CE}=4V, I_C=2A
Cob	-		200	pF	V_{CB}=10V, I_E=0A, f=1MHz

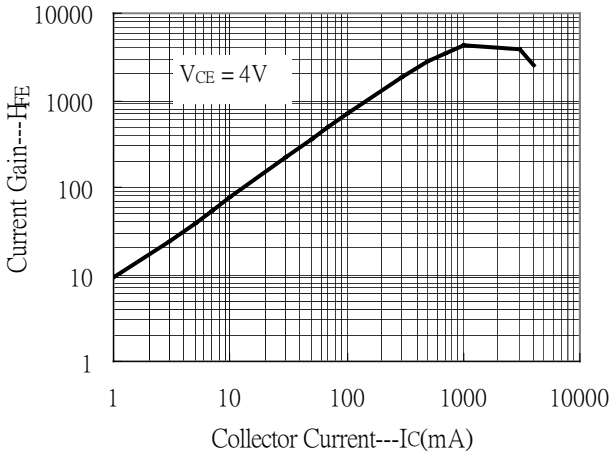
*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

Recommended soldering footprint

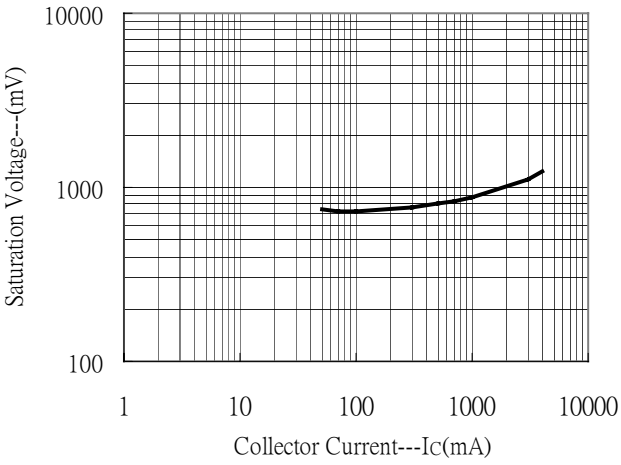


Characteristic Curves

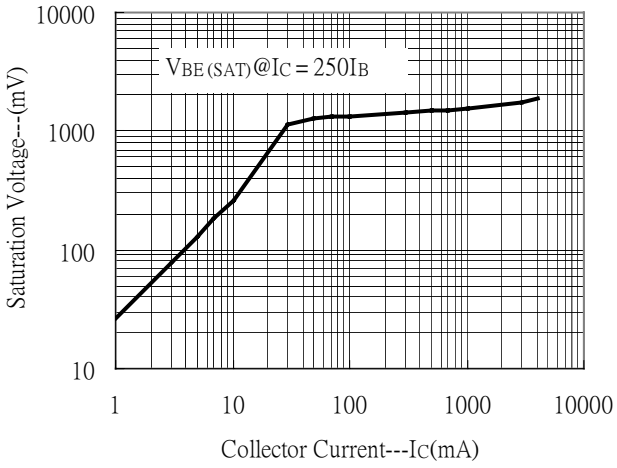
Current Gain vs Collector Current



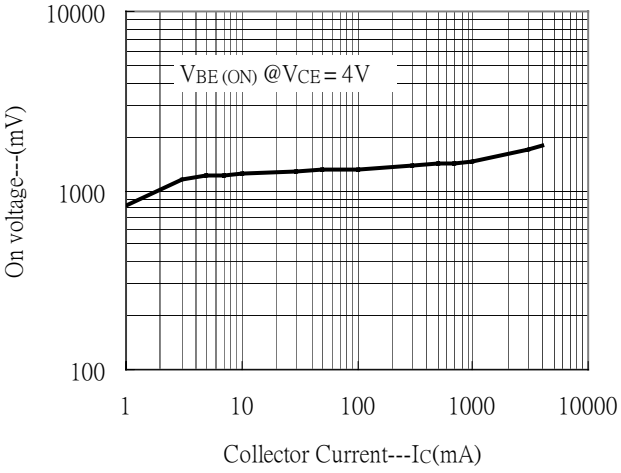
Saturation Voltage vs Collector Current



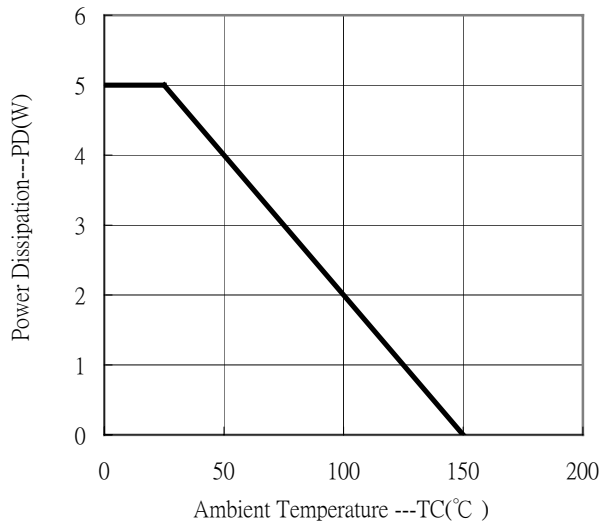
Saturation Voltage vs Collector Current



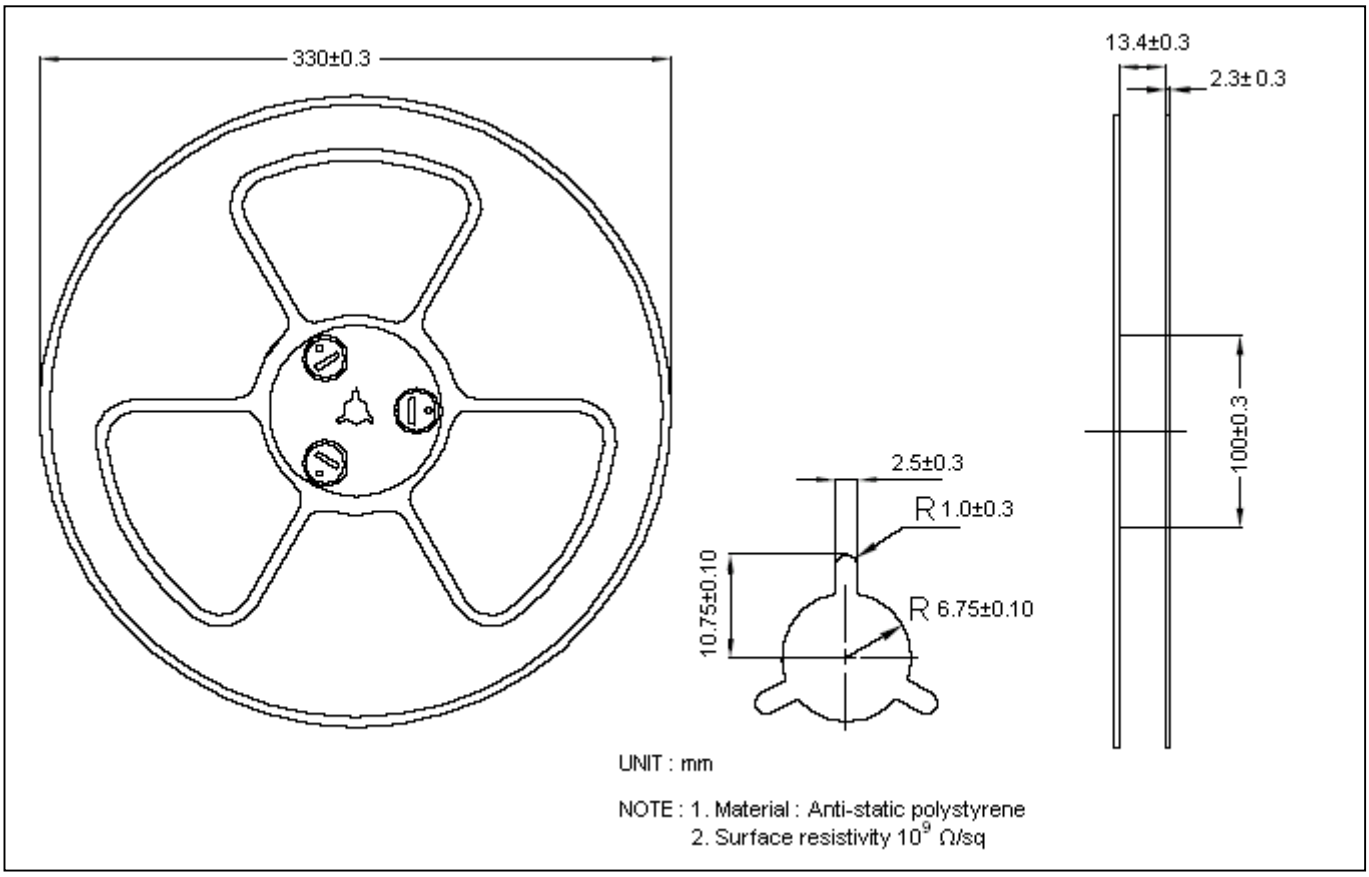
On voltage vs Collector Current



Power Derating Curve



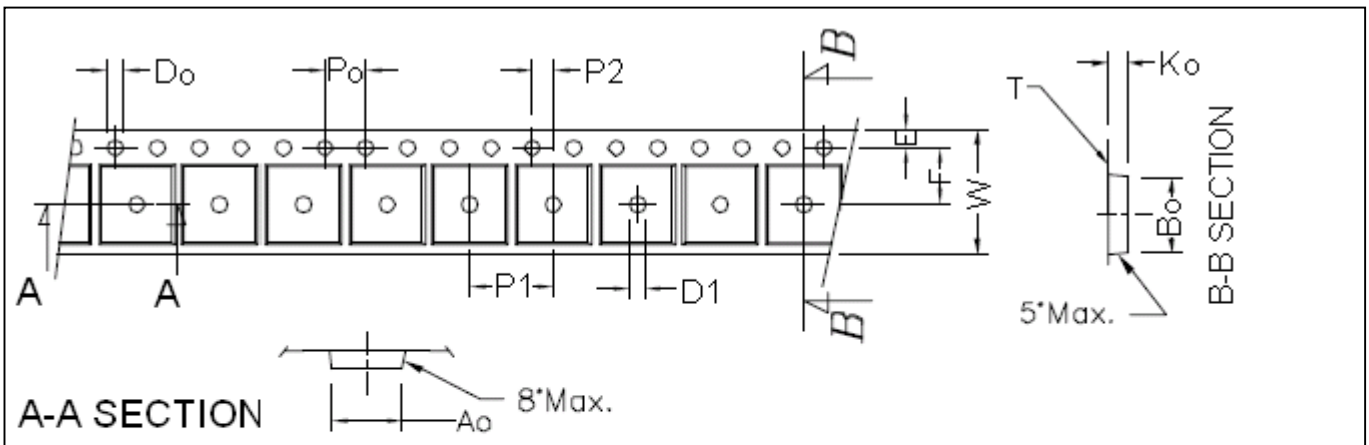
Reel Dimension



UNIT : mm

NOTE : 1. Material : Anti-static polystyrene
2. Surface resistivity 10^9 Ω/sq

Carrier Tape Dimension



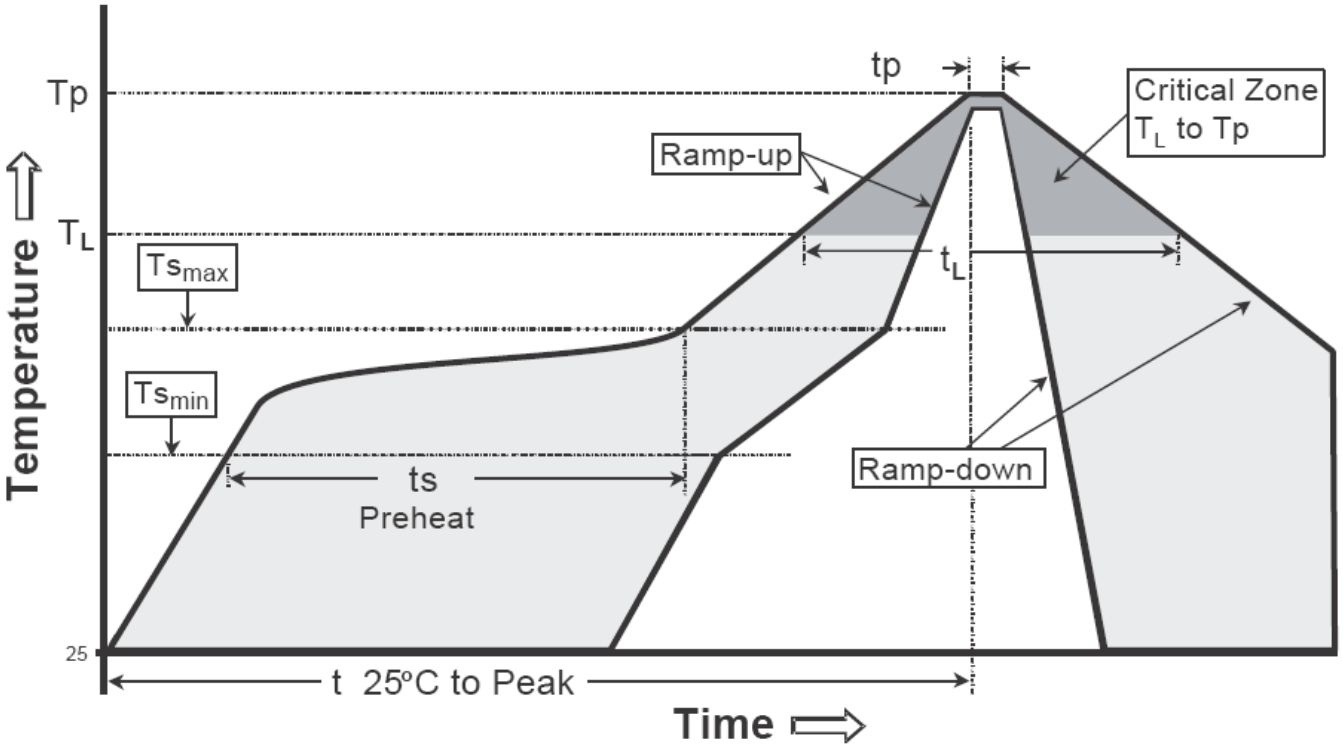
Symbol	Ao	Bo	Ko	Po	P1	P2	T
Spec	6.83±0.1	7.42±0.1	1.88±0.1	4.0±0.1	8.0±0.10	2.0±0.05	0.292±0.02
Symbol	E	F	Do	D1	W	10Po	
Spec	1.75±0.1	5.5±0.05	1.60±0.1	1.5±0.25	$12^{+0.3}_{-0.1}$	40.0±0.2	

Unit : mm

Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

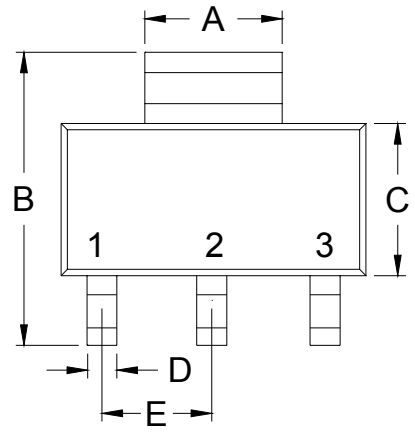
Recommended temperature profile for IR reflow

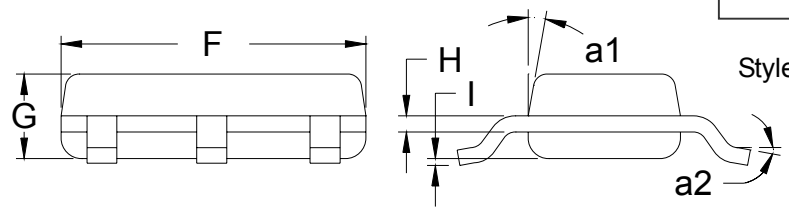


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(T_S min) −Temperature Max(T_S max) −Time($t_{s\ min}$ to $t_{s\ max}$)	 100°C 150°C 60-120 seconds	 150°C 200°C 60-180 seconds
Time maintained above: −Temperature (T_L) − Time (t_L)	 183°C 60-150 seconds	 217°C 60-150 seconds
Peak Temperature(T_P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

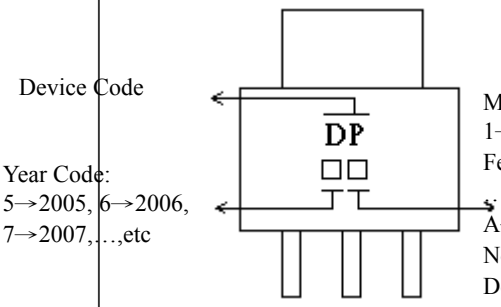
Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-223 Dimension





Marking:



Style: Pin 1.Base 2.Collector 3.Emitter

3-Lead SOT-223 Plastic
Surface Mounted Package
CYStek Package Code: L3

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1142	0.1220	2.90	3.10	G	0.0551	0.0709	1.40	1.80
B	0.2638	0.2874	6.70	7.30	H	0.0098	0.0138	0.25	0.35
C	0.1299	0.1457	3.30	3.70	I	0.0008	0.0039	0.02	0.10
D	0.0236	0.0315	0.60	0.80	a1	*13°	-	*13°	-
E	*0.0906	-	*2.30	-	a2	0°	10°	0°	10°
F	0.2480	0.2638	6.30	6.70					

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.